1200V 30A

Zero Recovery Silicon Carbide Schottky Diode

Microsemi.

PRODUCT APPLICATIONS

- Anti-Parallel Diode
 -Switchmode Power Supply
 -Inverters
- Power Factor Correction (PFC)

PRODUCT FEATURES

- Zero Recovery Times (t_{rr})
- Popular TO-247 Package or surface mount D³PAK package
- Low Forward Voltage
- Low Leakage Current

PRODUCT BENEFITS

- Higher Reliability Systems
- Minimizes or eliminates
 snubber



APT30SCD120B APT30SCD120S

1 - Cathode

 T_{C} = 25°C unless otherwise specified.

2 - Anode Back of Case - Cathode

MAXIMUM RATINGS

Symbol	Characteristic / Test Conditions		Ratings	Unit	
V _R	Maximum D.C. Reverse Voltage			Volts	
V _{RRM}	Maximum Peak Repetitive Reverse Voltage		1200		
V _{RWM}	Maximum Working Peak Reverse Voltage				
I _F	Maximum D.C. Forward current	T _c = 25°C	99	1	
		T _c = 135°C	29		
I _{FRM}	Repetitive Peak Forward Suge Current ($T_j = 45^{\circ}C$, $t_p = 10ms$, Half Sine Wave)		150	Amps	
I _{FSM}	Non-Repetitive Forward Surge Current (T _J = 25°C, t _p = 10ms, Half Sine)		330		
P _{tot}	Power Dissipation	T _c = 25°C	291	w	
		T _c = 125°C	93	VV	
Τ _J , Τ _{stg}	Operating and Storage Junction Temperature Range		-55 to 150	°C	
TL	Lead Temperature for 10 Seconds		300		

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions		Min	Тур	Мах	Unit
V _F	Forward Voltage	I _F = 30A T _J = 25°C		1.5	1.8	Volts
		I _F = 30A, T _J = 150°C		2.1		
I _{RM}	Maximum Reverse Leakage Current	V _R = 1200V T _J = 25°C			600	μΑ
		V _R = 1200V, T _J = 150°C			3000	
Q _c	Total Capactive Charge V _R = 800V, I _F = 30A, di/dt = -100A/ μ s, T _J = 25°C			200		nC
C _T	Junction Capacitance $V_{R} = 0V$, $T_{J} = 25^{\circ}C$, f = 1MHz			2100		pF
	Junction Capacitance V_{R} = 200V, T_{J} = 25°C, f = 1MHz			228		
	Junction Capacitance V_{R} = 400V, T_{J} = 25°C, f = 1MHz			167		

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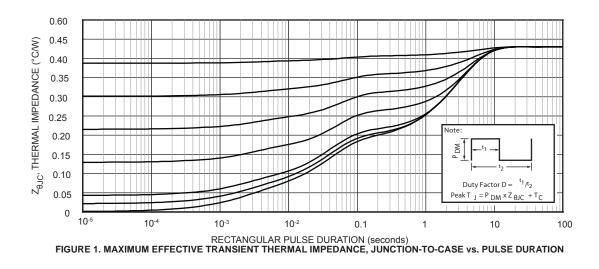
THERMAL AND MECHANICAL CHARACTERISTICS

APT30SCD120B S

Symbol	Characteristic / Test Conditions	Min	Тур	Мах	Unit
R _{ejc}	Junction-to-Case Thermal Resistance			0.43	°C/W
W _T	Package Weight		0.22		oz
			5.9		g
Torque	Maximum Mounting Torque			10	lb∙in
				1.1	N∙m

Microsemi reserves the right to change, without notice, the specifications and information contained herein.

TYPICAL PERFORMANCE CURVES



140 T_ = -55°C °C 120 I_F, FORWARD CURRENT (A) 100 T_J = 150°C 80 = 125°C 60 40 20 0 0 1 2 3 4 5 6 7 8 V_F, ANODE-TO-CATHODE VOLTAGE (V) FIGURE 2, Forward Current vs. Forward Voltage

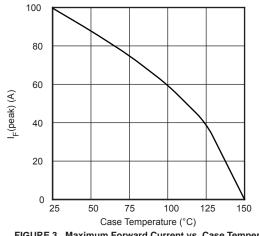
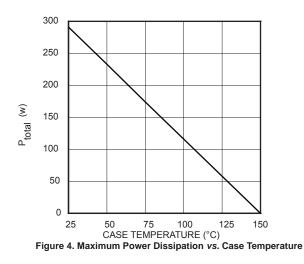
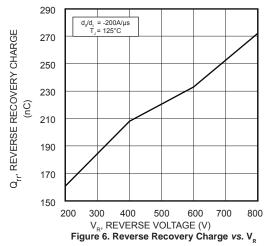
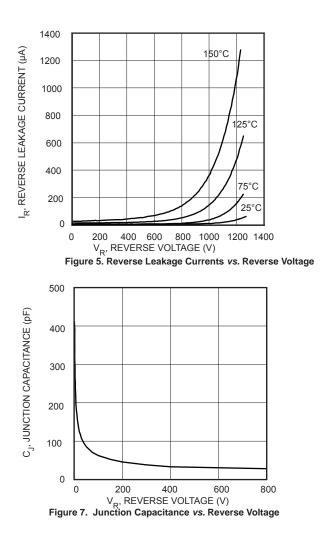


FIGURE 3, Maximum Forward Current vs. Case Temperature

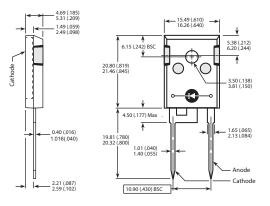




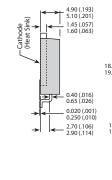


TO-247 Package Outline





Dimensions in Millimeters and (Inches)



15.85 (.624) 16.05(.632) 13.30 (.524) _ 13.60(.535) _ 1.00 (.039) 12.40 (.488) 12.70 (.500) 18.70 (.736) 19.10 (.752) ♦ 6 H 1.20 (.047) 1.40 (.055) 2.40 (.094) 2.70 (.106) (Base of Lead) 1.90 (.075) 2.10 (.083) 1.15 (.045) 1.45 (.057) Heat Sink (Cathode) and Leads are Plated 5.45 (.215) BSC (2 Plcs.) П Anode - Cathode

Dimensions in Millimeters and (Inches)

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